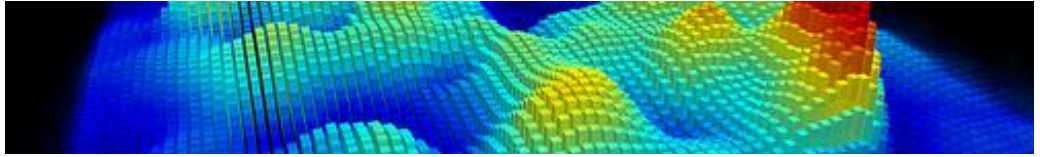




## Measurement of the surface electric potential of operating devices



keywords

Atomic Force  
 Microscope (AFM)  
 Surface electric  
 potential  
 Operating devices  
 Capacitance second  
 derivative  
 Semiconductors

Our laboratory has developed a new Atomic Force Microscopy (AFM) based technic to **accurately measure the surface electric potential profile** of devices in their **operating conditions (biased)**.

contact

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It is a **nondestructive** process.

Measurements can be performed in **ambient conditions**, thanks to :

- Using a dual pass method (lift)
- Synchronizing of the device and tip biasing with second pass only
- Using a force gradient sensitive method (EFM phase shift)

patented

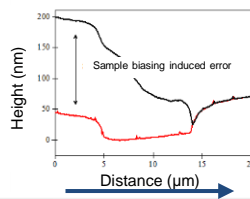
benefits

### Accurate and non-destructive method

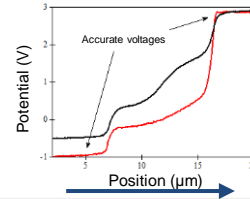
Thin film transistor application



topography



potential



— Current technology  
 — Our technology

applications

- Semiconductor device characterization
  - R&D
  - Quality Control
  - Fundamental research

Source of the technology

Pr Louis Giraudet  
 Laboratoire de Recherches en Nanosciences



development status

TRL5 : demo available in our lab

patent status

Patented



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